

N-channel TrenchMOS logic level FET Rev. 02 — 27 January 2011

Product data sheet

#### **Product profile** 1.

#### **1.1 General description**

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- 1.3 Applications
  - 12 V, 24 V and 42 V loads
  - Automotive and general purpose power switching

#### 1.4 Quick reference data

#### Table 1. Quick reference data

Suitable for logic level gate drive
sources

- Suitable for thermally demanding environments due to 175 °C rating
- Motors, lamps and solenoids

Parameter	Conditions	Min	Тур	Мах	Unit
drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	75	V
drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	45	A
total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	114	W
aracteristics					
drain-source on-state resistance	$V_{GS}$ = 4.5 V; $I_D$ = 25 A; $T_j$ = 25 °C	-	-	29	mΩ
	$V_{GS}$ = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	20.9	24.6	mΩ
	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see <u>Figure 13</u> ; see <u>Figure 12</u>	-	22.1	26	mΩ
ne ruggedness					
non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 49 \text{ A};  V_{sup} \leq 75 \text{ V}; \\ R_{GS} &= 50  \Omega;  V_{GS} = 5 \text{ V}; \\ T_{j(init)} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	120	mJ
	drain-source voltage drain current total power dissipation aracteristics drain-source on-state resistance non-repetitive drain-source	$\label{eq:generalized_set} \begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{cccc} \text{drain-source voltage} & T_j \geq 25 \ ^\circ\text{C}; \ T_j \leq 175 \ ^\circ\text{C} & - & - & 75 \\ \text{drain current} & V_{\text{GS}} = 5 \ ^\circ\text{Y}; \ T_{\text{mb}} = 25 \ ^\circ\text{C}; & - & - & 45 \\ \text{see Figure 1; see Figure 3} & - & - & 45 \\ \text{total power dissipation} & T_{\text{mb}} = 25 \ ^\circ\text{C}; \text{see Figure 2} & - & - & 114 \\ \hline \textbf{aracteristics} & & & & \\ \text{drain-source on-state} & V_{\text{GS}} = 4.5 \ ^\circ\text{Y}; \ I_D = 25 \ ^\circ\text{A}; \ T_j = 25 \ ^\circ\text{C} & - & - & 29 \\ \hline V_{\text{GS}} = 10 \ ^\circ\text{V}; \ I_D = 25 \ ^\circ\text{A}; \ T_j = 25 \ ^\circ\text{C} & - & 20.9 \\ \hline V_{\text{GS}} = 5 \ ^\circ\text{V}; \ I_D = 25 \ ^\circ\text{A}; \ T_j = 25 \ ^\circ\text{C}; & - & 20.9 \\ \hline \text{V}_{\text{GS}} = 5 \ ^\circ\text{V}; \ I_D = 25 \ ^\circ\text{A}; \ T_j = 25 \ ^\circ\text{C}; & - & 20.9 \\ \hline \textbf{V}_{\text{GS}} = 5 \ ^\circ\text{V}; \ I_D = 25 \ ^\circ\text{A}; \ T_j = 25 \ ^\circ\text{C}; & - & 20.9 \\ \hline \textbf{V}_{\text{GS}} = 5 \ ^\circ\text{V}; \ I_D = 25 \ ^\circ\text{C}; & - & 22.1 \ ^\circ\text{C}; \\ \text{see Figure 13; see Figure 12} & - & - & 120 \\ \hline \textbf{mon-repetitive} & I_D = 49 \ ^\circ\text{A}; \ V_{\text{Sup}} \leq 75 \ ^\circ\text{V}; & - & - & 120 \\ \hline \textbf{R}_{\text{GS}} = 50 \ ^\circ\text{Q}; \ V_{\text{GS}} = 5 \ ^\circ\text{V}; \end{array}$

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### 2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

### 3. Ordering information

#### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
BUK9226-75A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

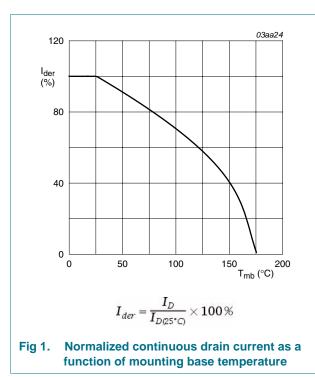
### 4. Limiting values

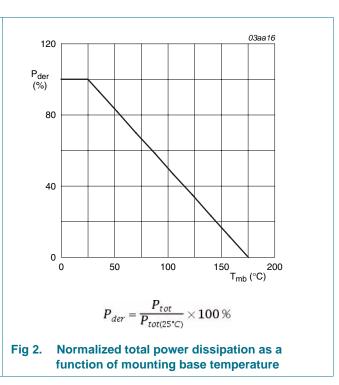
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Mox	l lni+
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	75	V
V <sub>DGR</sub>	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	75	V
V <sub>GS</sub>	gate-source voltage		-10	10	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	45	А
		$T_{mb}$ = 100 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u>	-	32	А
I <sub>DM</sub>	peak drain current	$T_{mb} = 25 \text{ °C}; \text{ pulsed}; t_p \le 10 \mu\text{s}; $ see <u>Figure 3</u>	1 -	182	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	114	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
V <sub>GSM</sub>	peak gate-source voltage	pulsed; t <sub>p</sub> ≤ 50 µs	-15	15	V
Source-drai	in diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	45	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	182	А
Avalanche I	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D = 49 \text{ A}; V_{sup} \le 75 \text{ V}; \text{ R}_{GS} = 50 \Omega;$ $V_{GS} = 5 \text{ V}; \text{ T}_{j(init)} = 25 \text{ °C}; \text{ unclamped}$	-	120	mJ

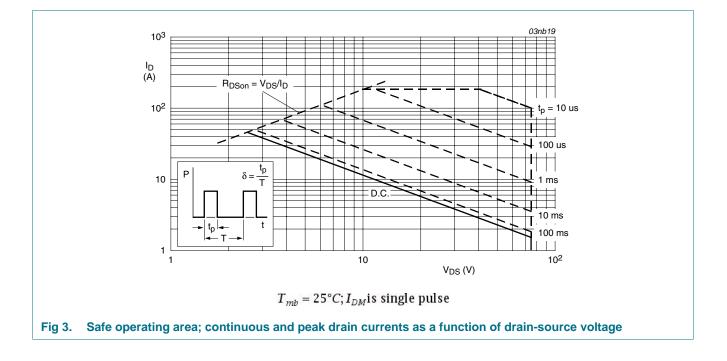
[1] Peak drain current is limited by chip, not package.





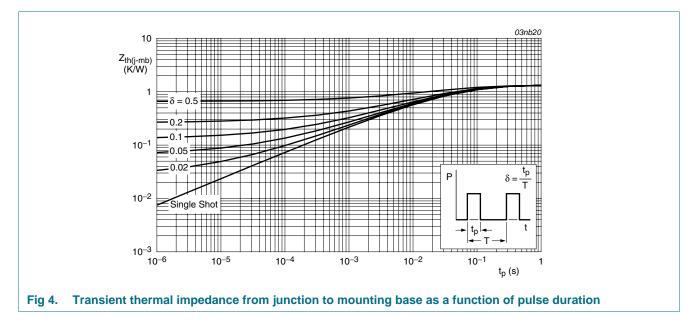
# BUK9226-75A

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### 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	-	1.3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint ; FR4 board	-	71.4	-	K/W



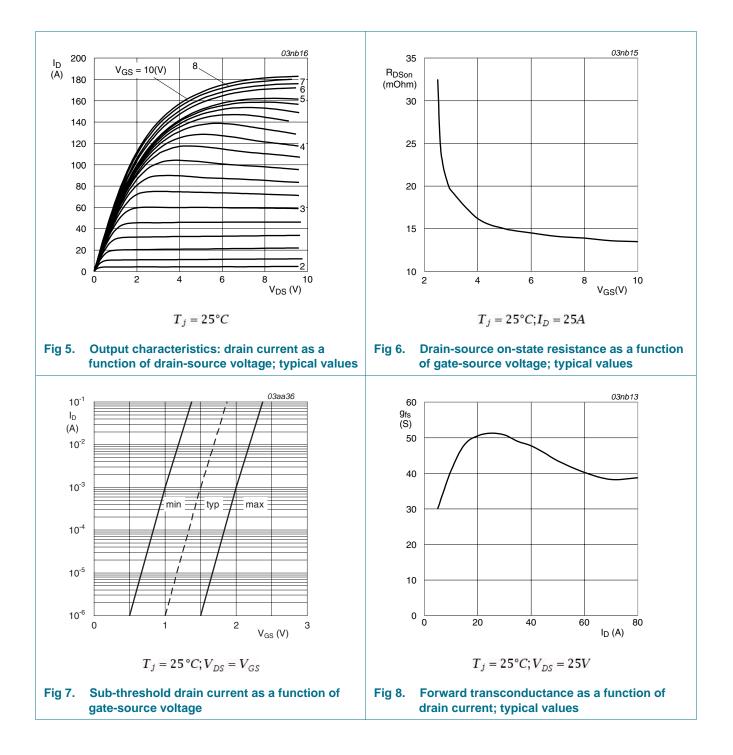
# Table 5. Thermal characteristics

### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D$ = 0.25 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	75	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	70	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; see <u>Figure 11</u>	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u>	1	1.5	2	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 11</u>	-	-	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -10 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	54.6	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	-	29	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	20.9	24.6	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 13; see Figure 12	-	22.1	26	mΩ
Dynamic	characteristics					
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	2340	3120	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	319	383	pF
C <sub>rss</sub>	reverse transfer capacitance		-	215	295	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}=30 \text{ V}; \text{ R}_{L}=1.2 \Omega; V_{GS}=5 \text{ V}; \label{eq:VDS}$	-	24	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \ \Omega; T_j = 25 \ ^{\circ}C$	-	141	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	142	-	ns
t <sub>f</sub>	fall time		-	108	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain lead from package to centre of die ; T <sub>j</sub> = 25 °C	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	measured from source lead from package to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 15</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$    I_S = 20 \text{ A}; \ dI_S/dt = 100 \text{ A}/\mu\text{s}; \\     V_{GS} = -10 \text{ V}; \ V_{DS} = 30 \text{ V}; \ T_j = 25 \ ^\circ\text{C} $	-	49	-	ns
Q <sub>r</sub>	recovered charge	I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 30 V; T <sub>i</sub> = 25 °C	-	115	-	nC

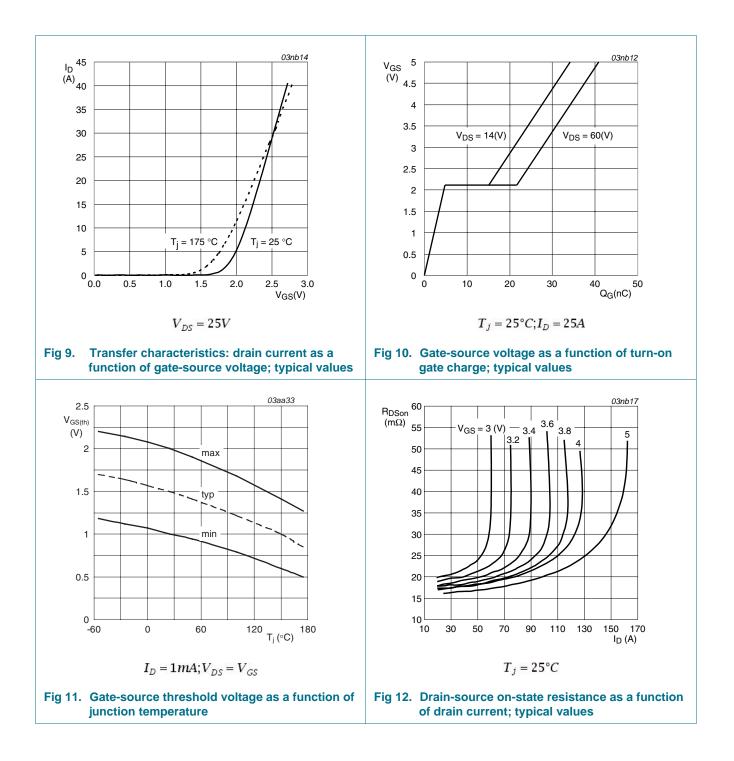
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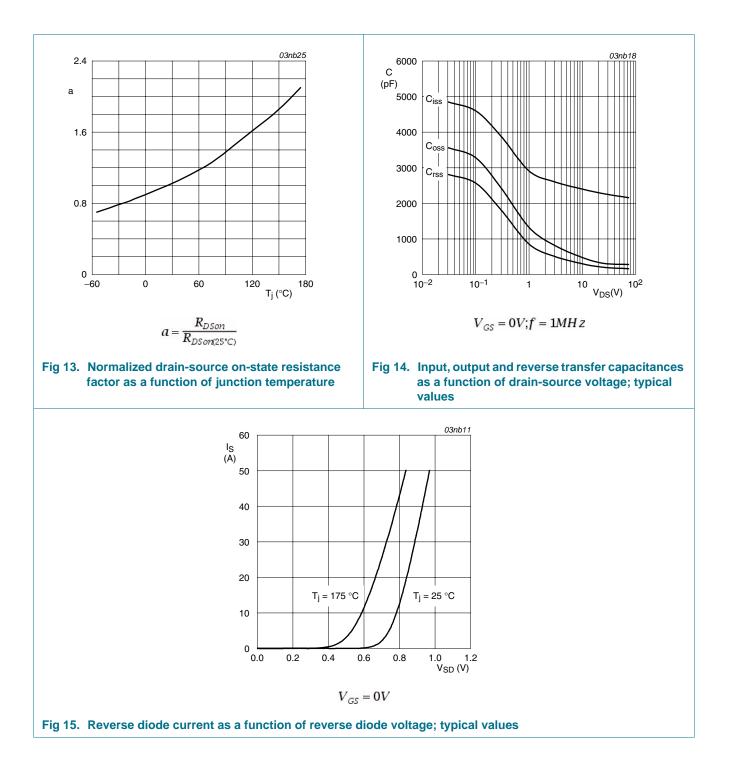
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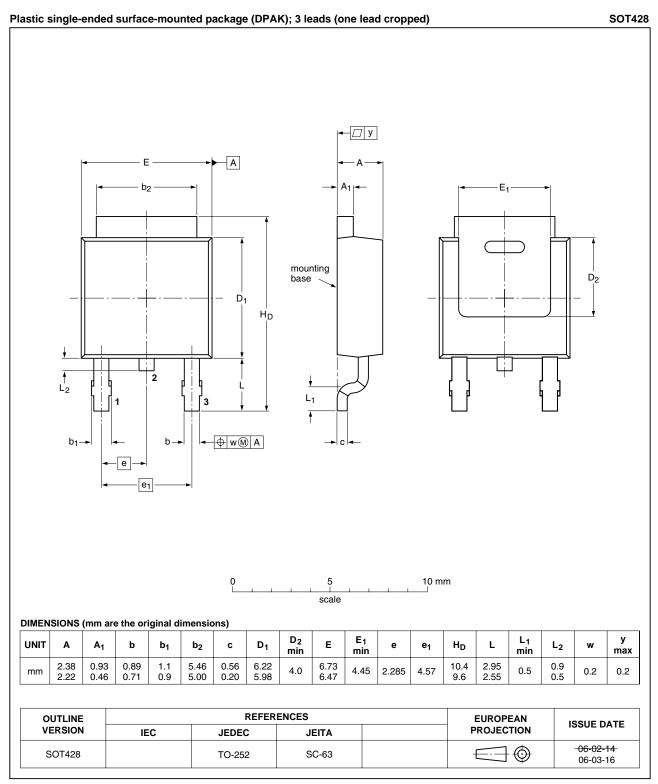
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### 7. Package outline



#### Fig 16. Package outline SOT428 (DPAK)

BUK9226-75A Product data sheet

### 8. Revision history

Table 7.Revision	history			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9226-75A v.2	20110127	Product data sheet	-	BUK9226_75A v.1
Modifications:	<ul> <li>The format of of NXP Semic</li> </ul>	this data sheet has been rec onductors.	designed to comply with	n the new identity guidelines
	<ul> <li>Legal texts hat</li> </ul>	ve been adapted to the new	company name where	appropriate.
BUK9226_75A v.1	20001010	Product specification	-	-

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#### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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